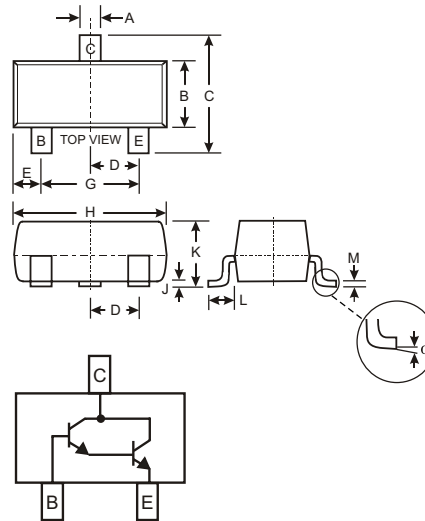


Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- High Current Gain

Mechanical Data

- Case: SOT-23, Molded Plastic
- Case Material - UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking (See Page 2): K6R
- Weight: 0.008 grams (approx.)
- Ordering & Date Code Information: See Page 2



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MMBTA28	Unit
Collector-Base Voltage	V_{CB0}	80	V
Collector-Emitter Voltage	V_{CE0}	80	V
Emitter-Base Voltage	V_{EB0}	12	V
Collector Current - Continuous	I_C	500	mA
Power Dissipation	P_d	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	80	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	12	—	V	$I_E = 100\mu\text{A}, I_C = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80	—	V	$I_C = 100\mu\text{A}, I_B = 0$
Collector Cutoff Current	I_{CBO}	—	100	nA	$V_{CB} = 60\text{V}, I_E = 0$
Emitter Cutoff Current	I_{EBO}	—	100	nA	$V_{EB} = 10\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	10,000 10,000	—	—	$I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 5.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	1.5	V	$I_C = 100\text{mA}, I_B = 100\mu\text{A}$
Base- Emitter Saturation Voltage	$V_{BE(SAT)}$	—	2.0	V	$I_C = 100\text{mA}, V_{CE} = 5.0\text{V}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	8.0 Typical	—	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	15 Typical	—	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Current Gain-Bandwidth Product	f_T	125	—	MHz	$V_{CE} = 5.0\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$

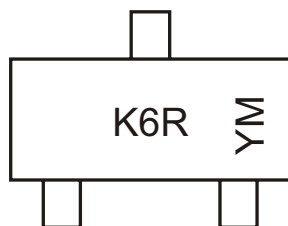
Notes: 1. Device mounted on FR-4 PCB, 1.6x1.6x0.06 nch pad layout as shown on Diodes Inc. suggested pad layout document AP02001 which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
2. Short duration test pulse used to minimize self-heating effect.

Ordering Information (Note 3)

Device	Packaging	Shipping
MMBTA28-7	SOT-23	3000/Tape & Reel

Notes: 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



K6R = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

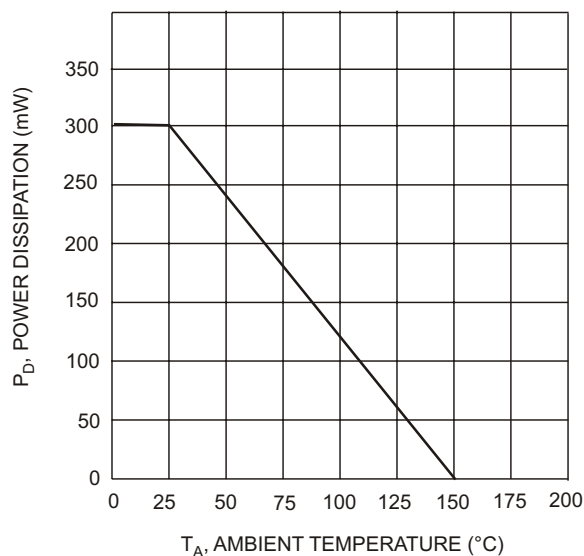


Fig. 1, Max Power Dissipation vs Ambient Temperature

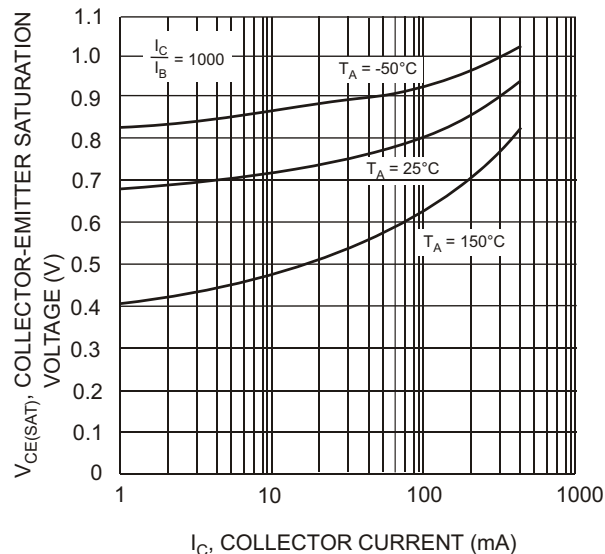
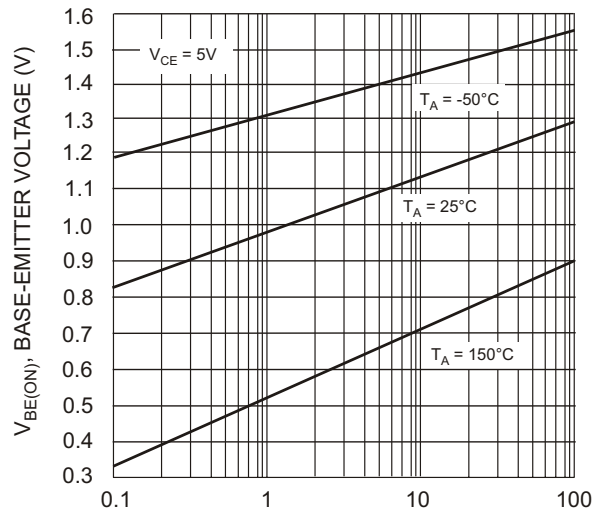
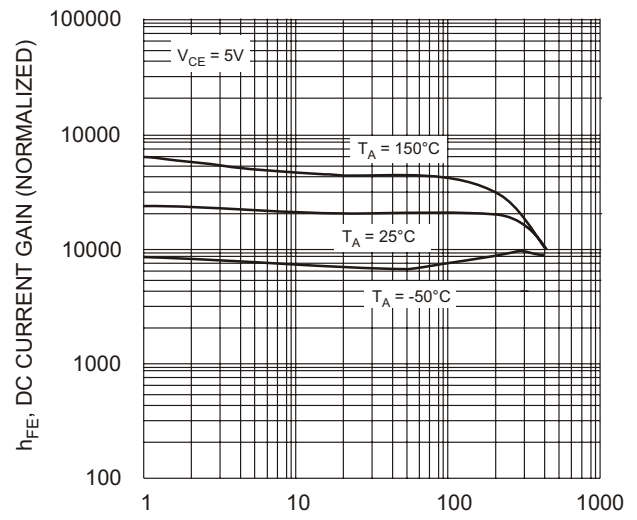


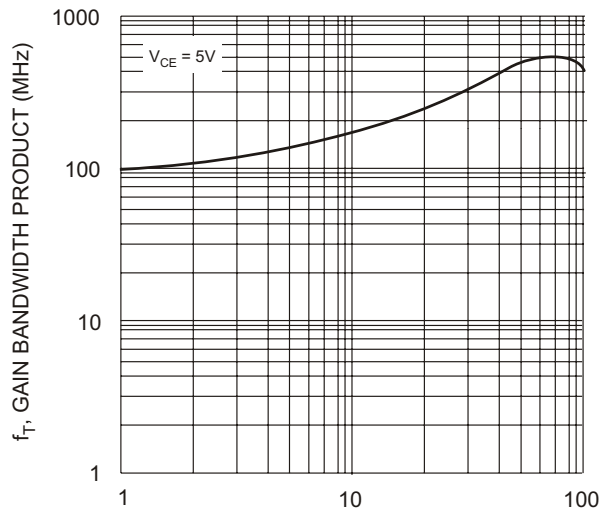
Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 3 Typical Base-Emitter Voltage
vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 4 Typical DC Current Gain
vs. Collector Current



COLLECTOR CURRENT I_C (mA)
Fig. 5 Typical Gain Bandwidth Product
vs. Collector Current